REVISIONS			
LTR	DESCRIPTION	DATE (YR-MO-DA)	APPROVED
A	Add device type 02. Technical and editorial changes throughout.	94-05-24	M.A. Frye
B	Add device type 03. Technical and editorial changes throughout.	95-08-16	M.A. Frye

REV																			
SHEET																			
REV																			
SHEET																			

REV STATUS OF SHEETS	REV	B	B	B	B	B	B	B	B	B	B	B	B	B	B
	SHEET	1	2	3	4	5	6	7	8	9	10	11	12	13	

PMIC N/A

STANDARD MICROCIRCUIT DRAWING

THIS DRAWING IS AVAILABLE FOR USE BY ALL DEPARTMENTS AND AGENCIES OF THE DEPARTMENT OF DEFENSE

AMSC N/A

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DRAWING APPROVAL DATE
94-03-08

REVISION LEVEL
B

DEFENSE ELECTRONICS SUPPLY CENTER
DAYTON, OHIO 45444

MICROCIRCUIT, LINEAR, VOLTAGE REGULATOR, HIGH POWER FACTOR, MONOLITHIC SILICON

SIZE	CAGE CODE	
A	67268	**5962-93261**

SHEET 1 OF 13

DESC FORM 193
JUL 94

5962-E227-95

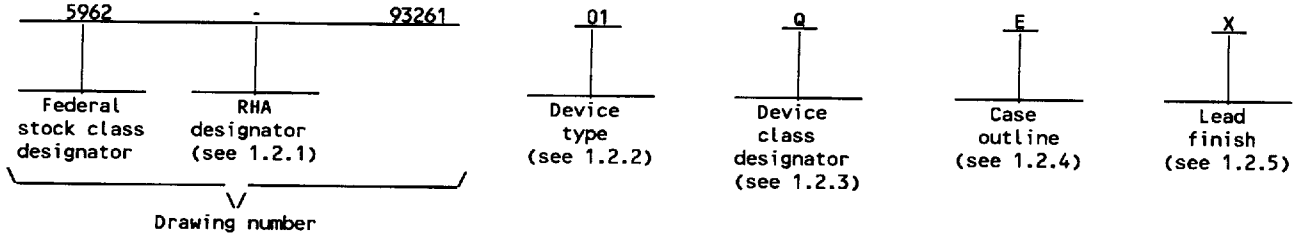
DISTRIBUTION STATEMENT A Approved for public release; distribution is unlimited.

9004708 0013418 T45

1. SCOPE

1.1 Scope. This drawing forms a part of a one part - one part number documentation system (see 6.6 herein). Two product assurance classes consisting of military high reliability (device classes Q and M) and space application (device class V), and a choice of case outlines and lead finishes are available and are reflected in the Part or Identifying Number (PIN). Device class M microcircuits represent non-JAN class B microcircuits in accordance with 1.2.1 of MIL-STD-883, "Provisions for the use of MIL-STD-883 in conjunction with compliant non-JAN devices". When available, a choice of Radiation Hardness Assurance (RHA) levels are reflected in the PIN.

1.2 PIN. The PIN shall be as shown in the following example:



1.2.1 RHA designator. Device class M RHA marked devices shall meet the MIL-I-38535 appendix A specified RHA levels and shall be marked with the appropriate RHA designator. Device classes Q and V RHA marked devices shall meet the MIL-I-38535 specified RHA levels and shall be marked with the appropriate RHA designator. A dash (-) indicates a non-RHA device.

1.2.2 Device type(s). The device type(s) shall identify the circuit function as follows:

Device type	Generic number	Circuit function
01	UC1854	Voltage preregulator, high power factor
02	UC1854B	Voltage preregulator, high power factor
03	UC1854A	Voltage preregulator, high power factor

1.2.3 Device class designator. The device class designator shall be a single letter identifying the product assurance level as follows:

Device class	Device requirements documentation
M	Vendor self-certification to the requirements for non-JAN class B microcircuits in accordance with 1.2.1 of MIL-STD-883
Q or V	Certification and qualification to MIL-I-38535

1.2.4 Case outline(s). The case outline(s) shall be as designated in MIL-STD-1835 and as follows:

Outline letter	Descriptive designator	Terminals	Package style
E	GDIP1-T16 or CDIP2-T16	16	dual-in-line
2	CQCC1-N20	20	square leadless chip carrier

1.2.5 Lead finish. The lead finish shall be as specified in MIL-STD-883 (see 3.1 herein) for class M or MIL-I-38535 for classes Q and V. Finish letter "X" shall not be marked on the microcircuit or its packaging. The "X" designation is for use in specifications when lead finishes A, B, and C are considered acceptable and interchangeable without preference.

1.3 Absolute maximum ratings. 1/ 2/ 3/

Supply voltage (V_{CC}):	
Device type 01	35 V dc
Device type 02 and 03	22 V dc
GTDRV current, continuous	0.5 A
GTDRV current, 50 percent duty cycle	1.5 A
Input voltage, V_{SENSE}, V_{RMS}	11 V dc
Input voltage, I_{SENSE}, $MULT_{OUT}$	11 V dc
Input voltage, PKLMT	5 V dc
Input current, R_{SET}, IAC, ENA, PKLMT	10 mA
Power dissipation, T_A = +25°C (P_D)	1 W 4/
Thermal resistance, junction-to-case (Θ_{JC})	See MIL-STD-1835
Thermal resistance, junction-to-ambient (Θ_{JA})	80°C/W
Storage temperature range	-65°C to +150°C
Lead temperature (soldering, 10 seconds)	+300°C
Junction temperature (T_J)	+150°C

1.4 Recommended operating conditions.

Supply voltage	18 V dc
Ambient operating temperature range (T_A)	-55°C to +125°C

2. APPLICABLE DOCUMENTS

2.1 Government specification, standards, bulletin, and handbook. Unless otherwise specified, the following specification, standards, bulletin, and handbook of the issue listed in that issue of the Department of Defense Index of Specifications and Standards specified in the solicitation, form a part of this drawing to the extent specified herein.

SPECIFICATION

MILITARY

MIL-I-38535 - Integrated Circuits, Manufacturing, General Specification for.

STANDARDS

MILITARY

MIL-STD-883 - Test Methods and Procedures for Microelectronics.
MIL-STD-973 - Configuration Management.
MIL-STD-1835 - Microcircuit Case Outlines.

BULLETIN

MILITARY

MIL-BUL-103 - List of Standard Microcircuit Drawings (SMD's).

HANDBOOK

MILITARY

MIL-HDBK-780 - Standardized Military Drawings.

(Copies of the specification, standards, bulletin, and handbook required by manufacturers in connection with specific acquisition functions should be obtained from the contracting activity or as directed by the contracting activity.)

1/ Stresses above the absolute maximum rating may cause permanent damage to the device. Extended operation at the maximum levels may degrade performance and affect reliability.
2/ All voltages with respect to GND.
3/ All currents are positive into the specified terminal.
4/ Derate 8 mW/°C for T_A > +25°C.

2.2 Order of precedence. In the event of a conflict between the text of this drawing and the references cited herein, the text of this drawing shall take precedence.

3. REQUIREMENTS

3.1 Item requirements. The individual item requirements for device class M shall be in accordance with 1.2.1 of MIL-STD-883, "Provisions for the use of MIL-STD-883 in conjunction with compliant non-JAN devices" and as specified herein. The individual item requirements for device classes Q and V shall be in accordance with MIL-I-38535 and as specified herein or as modified in the device manufacturer's Quality Management (QM) plan. The modification in the QM plan shall not effect the form, fit, or function as described herein.

3.2 Design, construction, and physical dimensions. The design, construction, and physical dimensions shall be as specified in MIL-STD-883 (see 3.1 herein) for device class M and MIL-I-38535 for device classes Q and V and herein.

3.2.1 Case outline(s). The case outline(s) shall be in accordance with 1.2.4 herein.

3.2.2 Terminal connections. The terminal connections shall be as specified on figure 1.

3.2.4 Block diagram(s). The block diagram(s) shall be as specified on figure 2.

3.3 Electrical performance characteristics and postirradiation parameter limits. Unless otherwise specified herein, the electrical performance characteristics and postirradiation parameter limits are as specified in table I and shall apply over the full ambient operating temperature range.

3.4 Electrical test requirements. The electrical test requirements shall be the subgroups specified in table II. The electrical tests for each subgroup are defined in table I.

3.5 Marking. The part shall be marked with the PIN listed in 1.2 herein. Marking for device class M shall be in accordance with MIL-STD-883 (see 3.1 herein). In addition, the manufacturer's PIN may also be marked as listed in MIL-BUL-103. Marking for device classes Q and V shall be in accordance with MIL-I-38535.

3.5.1 Certification/compliance mark. The compliance mark for device class M shall be a "C" as required in MIL-STD-883 (see 3.1 herein). The certification mark for device classes Q and V shall be a "QML" or "Q" as required in MIL-I-38535.

3.6 Certificate of compliance. For device class M, a certificate of compliance shall be required from a manufacturer in order to be listed as an approved source of supply in MIL-BUL-103 (see 6.7.2 herein). For device classes Q and V, a certificate of compliance shall be required from a QML-38535 listed manufacturer in order to supply to the requirements of this drawing (see 6.7.1 herein). The certificate of compliance submitted to DESC-EC prior to listing as an approved source of supply for this drawing shall affirm that the manufacturer's product meets, for device class M, the requirements of MIL-STD-883 (see 3.1 herein), or for device classes Q and V, the requirements of MIL-I-38535 and the requirements herein.

3.7 Certificate of conformance. A certificate of conformance as required for device class M in MIL-STD-883 (see 3.1 herein) or for device classes Q and V in MIL-I-38535 shall be provided with each lot of microcircuits delivered to this drawing.

3.8 Notification of change for device class M. For device class M, notification to DESC-EC of change of product (see 6.2 herein) involving devices acquired to this drawing is required for any change as defined in MIL-STD-973.

3.9 Verification and review for device class M. For device class M, DESC, DESC's agent, and the acquiring activity retain the option to review the manufacturer's facility and applicable required documentation. Offshore documentation shall be made available onshore at the option of the reviewer.

3.10 Microcircuit group assignment for device class M. Device class M devices covered by this drawing shall be in microcircuit group number 52 (see MIL-I-38535, appendix A).

4. QUALITY ASSURANCE PROVISIONS

4.1 Sampling and inspection. For device class M, sampling and inspection procedures shall be in accordance with MIL-STD-883 (see 3.1 herein). For device classes Q and V, sampling and inspection procedures shall be in accordance with MIL-I-38535 or as modified in the device manufacturer's Quality Management (QM) plan. The modification in the QM plan shall not effect the form, fit, or function as described herein.

4.2 Screening. For device class M, screening shall be in accordance with method 5004 of MIL-STD-883, and shall be conducted on all devices prior to quality conformance inspection. For device classes Q and V, screening shall be in accordance with MIL-I-38535, and shall be conducted on all devices prior to qualification and technology conformance inspection.

TABLE I. Electrical performance characteristics.

Test	Symbol	Conditions 1/ $-55°C \le T_A \le +125°C$ unless otherwise specified	Group A subgroups	Device type	Limits Min	Limits Max	Unit
OVERALL SECTION							
Supply current, Off	$I_{CC\ OFF}$	ENA = 0 V	1, 2, 3	01		2.0	mA
		CA_{OUT} = 0 V, VA_{OUT} = 0 V, V_{CC} = UVLO - 0.3 V		02, 03		0.4	
Supply current, On	$I_{CC\ ON}$		1, 2, 3	01		16	mA
				02, 03		18	
V_{CC} turn-on threshold	VT_{ON}		1, 2, 3	01	14.5	17.5	V
				02		11.2	
				03		17.5	
V_{CC} turn-off threshold	VT_{OFF}		1, 2, 3	01	9	11	V
				02, 03	9		
ENA threshold, rising	$ENAT_R$		1, 2, 3	01	2.4	2.7	V
				02, 03	2.5	2.8	
ENA threshold hysteresis	$ENAT_H$		1, 2, 3	01	0.2	0.3	V
		V_{FAULT} = 2.5 V		02, 03	.35	0.6	
ENA input current	$ENAI_{IN}$	ENA = 0 V	1, 2, 3	All	-5.0	+5.0	µA
V_{RMS} input current	RMS_{IN}	V_{RMS} = 5 V	1, 2, 3	01	-1.0	+1.0	µA
V_{CC} clamp voltage	V_{CMP}	I (V_{CC}) = $I_{CC(on)}$ + 5 mA	1, 2, 3	02, 03	18	22	V
VOLTAGE AMPLIFIER SECTION							
Voltage Amp offset voltage	V_{AO}	VA_{OUT} = 3.5 V	1, 2, 3	01	-8	+8	mV
Voltage Amp input voltage	V_{IA}		1, 2, 3	02, 03	2.9	3.1	V
Voltage Amp V_{OUT} high	V_{OAH}	I_{LOAD} = -500 µA	1, 2, 3	02, 03	4		V
Voltage Amp V_{OUT} low	V_{OAL}	I_{LOAD} = 500 µA	1, 2, 3	02, 03		0.5	V
V_{SENSE} bias current	I_B	V_{SENSE} = 0 V	1, 2, 3	All	-500	500	nA
Voltage amp output swing	V_{AOS}		1, 2, 3	01	0.5 to 5		V

See footnotes at end of table.

TABLE I. Electrical performance characteristics - Continued.

Test	Symbol	Conditions 1/ $-55°C \le T_A \le +125°C$ unless otherwise specified	Group A subgroups	Device type	Limits		Unit
					Min	Max	
VOLTAGE AMPLIFIER SECTION - Continued							
Voltage amp gain	A_{VA}		1, 2, 3	All	70		dB
Voltage amp short circuit current	I_{ASC}	VA_{OUT} = 0 V	1, 2, 3	01	5	30	mA
				02, 03		3.5	
SS current	I_{SS}	SS = 2.5 V	1, 2, 3	01	6	20	µA
				02,03	10	24	
CURRENT AMPLIFIER SECTION							
Current amp input offset voltage	V_{IAO}	V_{CM} = 0 V	1, 2, 3	01	-4	+4	mV
				02, 03	-4	0	
Current Amp output voltage high	I_{OAH}	I_{LOAD} = -500 µA	1, 2, 3	02, 03	6		V
Voltage Amp output voltage low	I_{OAL}	I_{LOAD} = 500 µA	1, 2, 3	02, 03		0.5	V
I_{SENSE} bias current	I_B	V_{CM} = 0 V	1, 2, 3	All	-500	500	nA
Current amp gain	A_{IA}	V_{CM} = 0 V, V_{OUT} = 2 to 6 V	1, 2, 3	All	80		dB
Current amp output voltage swing	V_{AOS}		1, 2, 3	01	0.5 to 16		V
Current amp short circuit current	I_{ASC}	CA_{OUT} = 0 V	1, 2, 3	01	5	30	mA
				02, 03		3.5	
Current amp input voltage range I_{SENSE}, $MULT_{OUT}$	V_{INR}		1, 2, 3	01	-0.3 to 1.0		V
				02, 03	-0.3 to 5.0		
REFERENCE SECTION							
Reference output voltage	VOUTR	I_{REF} = 0 mA	1	All	7.4	7.6	V
			2, 3		7.35	7.65	
V_{REF} load regulation	V_{RLOAD}	-10 mA $\le I_{REF} \le$ 0 mA	1, 2, 3	01	-15	+15	mV
				02, 03	0	+20	
V_{REF} short circuit current	I_{SC}	V_{REF} = 0 V	1, 2, 3	01	12	50	mA
				02, 03	25	45	

See footnotes at end of table.

TABLE I. Electrical performance characteristics - Continued.

Test	Symbol	Conditions 1/ $-55°C \le T_A \le +125°C$ unless otherwise specified	Group A subgroups	Device type	Limits		Unit
					Min	Max	
REFERENCE SECTION - Continued							
V_{REF} line regulation	V_{RLINE}	$15 V \le V_{CC} \le 35 V$	1, 2, 3	01	-10	+10	mV
		$12 V \le V_{CC} \le 18 V$	1, 2, 3	02, 03	0	+25	mV
CURRENT LIMIT SECTION							
PKLMT offset voltage	V_{OPKLMT}		1, 2, 3	01	-10	+10	mV
				02, 03	-15	+15	
PKLMT input current	I_{IPKLMT}	PKLMT = -0.1 V	1, 2, 3	All	-200		µA
GATE DRIVER SECTION							
Maximum GTDRV output voltage	V_{OGTDRV}	0 mA load on GTDRV, $18 V \le V_{CC} \le 35 V$	1, 2, 3	01	13	18	V
GTDRV output voltage high	V_{OHTDRV}	-200 mA load on GTDRV, V_{CC} = 15 V	1, 2, 3	All	12		V
GTDRV output voltage low, OFF	V_{OLDRV1}	50 mA load on GTDRV, V_{CC} = 0 V	1, 2, 3	All		1.5	V
GTDRV output voltage low	V_{OLDRV2}	200 mA load on GTDRV	1, 2, 3	All		2.2	V
GTDRV output voltage low	V_{OLDRV3}	10 mA load on GTDRV	1, 2, 3	02, 03		500	mV
MULTIPLIER SECTION							
Multiplier output current full scale	I_{MOFS}	V_{RMS} = 1 V, R_{SET} = 10 kΩ, IAC = 100 µA	1, 2, 3	01	-220	-180	µA
				02,03	-220	-170	
Multiplier output current zero	I_{MOZ}	IAC = 0 µA, R_{SET} = 15 kΩ	1, 2, 3	All	-2.0	+2.0	µA
Multiplier maximum output current	I_{MMO}	IAC = 450 µA, R_{SET} = 15 kΩ	1, 2, 3	01	-280	-220	µA
Multiplier maximum output current, power limited	I_{MMOL}	V_{RMS} = 1.5 V, VA_{OUT} = 6 V	1, 2, 3	02, 03	-230	-170	µA
Multiplier gain constant	A_{MG}	V_{RMS} = 1.5 V, VA_{OUT} = 6 V, T_A = +25°C 2/	1	02, 03	-1.1	-0.9	A/A

See footnotes at end of table.

TABLE I. Electrical performance characteristics - Continued.

Test	Symbol	Conditions 1/ $-55°C \le T_A \le +125°C$ unless otherwise specified	Group A subgroups	Device type	Limits		Unit
					Min	Max	
MULTIPLIER SECTION - Continued							
Multiplier output current	I_{MO}	IAC = 50 µA, V_{RMS} = 2 V, VA_{OUT} = 4 V	1, 2, 3	01	-50	-33	µA
		IAC = 100 µA, V_{RMS} = 2 V, VA_{OUT} = 2 V			-38	-12	
		IAC = 200 µA, V_{RMS} = 2 V, VA_{OUT} = 4 V			-165	-105	
		IAC = 300 µA, V_{RMS} = 1 V, VA_{OUT} = 2 V			-250	-150	
		IAC = 100 µA, V_{RMS} = 1 V, VA_{OUT} = 2 V			-95	-60	
		V_{RMS} = 1.5 V, VA_{OUT} = 2 V		02, 03	-44	0	
		V_{RMS} = 1.5 V, VA_{OUT} = 5 V			-256	56	
		V_{RMS} = 5 V, VA_{OUT} = 2 V			-15	0	
		V_{RMS} = 5 V, VA_{OUT} = 5 V			-35	0	
OSCILLATOR SECTION							
Oscillator frequency	OSC_F	R_{SET} = 15 kΩ	4, 5, 6	01	46	62	kHz
		R_{SET} = 8.2 kΩ			86	118	
CT ramp peak-to-peak amplitude	V_{CTPP}		4, 5, 6	All	4.9	5.9	V
Oscillator initial accuracy	---	T_A = +25°C	4	02, 03	85	115	kHz
Oscillator total variation	---		4, 5, 6	02, 03	80	120	kHz
Ramp valley voltage	---		4, 5, 6	02, 03	0.8	1.3	V

1/ V_{CC} = 18 V, R_{SET} = 8.2 kΩ to GROUND, C_T = 1.5 nF to GROUND, PKLMT = 1 V, ENA = 7.5 V, V_{RMS} = 1.5 V, IAC = 100 µA, I_{SENSE} = 0 V, CA_{OUT} = 4 V, VA_{OUT} = 3.5 V, V_{SENSE} = 3 V, no load on any output, $T_A = T_J$.

2/ Gain constant (K) = I_{AC} X (VA_{OUT} - 1.5 V/V_{RMS}2 X I_{MO}).

Case outline	E	2
Device type	01, 02, and 03	
Terminal number	Terminal symbol	
1	GND	NC
2	PKLMT	GND
3	CA_{OUT}	PKLMT
4	I_{SENSE}	CA_{OUT}
5	$MULT_{OUT}$	I_{SENSE}
6	IAC	NC
7	VA_{OUT}	$MULT_{OUT}$
8	V_{RMS}	IAC
9	V_{REF}	VA_{OUT}
10	ENA	V_{RMS}
11	V_{SENSE}	NC
12	R_{SET}	V_{REF}
13	SS	ENA
14	CT	V_{SENSE}
15	V_{CC}	R_{SET}
16	GTDRV	NC
17	---	SS
18	---	CT
19	---	V_{CC}
20	---	GTDRV

GND - all voltages are measured with respect to GROUND.
PKLMT - peak limit, the threshold for PKLMT is GROUND.
CA_{OUT} - current amplifier output.
V_{SENSE} - voltage amplifier inverting input.
R_{SET} - oscillator charging current and multiplier limit set.
SS - soft start.
CT - Oscillator timing capacitor
V_{CC} - positive supply voltage.
I_{SENSE} - current sense minus, the inverting input to the current amplifier.
$MULT_{OUT}$ - multiplier output and current sense plus, the output of the analog multiplier and the non-inverting input of the current amplifier are connected together at $MULT_{OUT}$.
IAC - input ac current, input to the analog multiplier is a current.
GTDRV - gate drive, the output of the PWM is a totem pole MOSFET gate driver on GTDRV.
VA_{OUT} - voltage amplifier output, the output of the op amp that regulates output voltage.
ENA - enable, a logic input that will enable the PWM output, voltage reference, and oscillator. ENA will also release the soft start clamp, allowing SS to rise.
V_{RMS} - RMS line voltage, the output of a boost PWM is proportional to the input voltage, so when the line voltage into a low- bandwidth boost PWM voltage regulator changes, the output will change immediately and slowly recover to the regulated level.
REF - voltage reference output, the output of an accurate 7.5 V voltage reference. It is capable of delivering 10 mA to peripheral circuitry and is internally short circuit current limited. REF is disabled and will remain at 0 V when V_{CC} is low or when ENA is low.

FIGURE 1. Terminal connections.

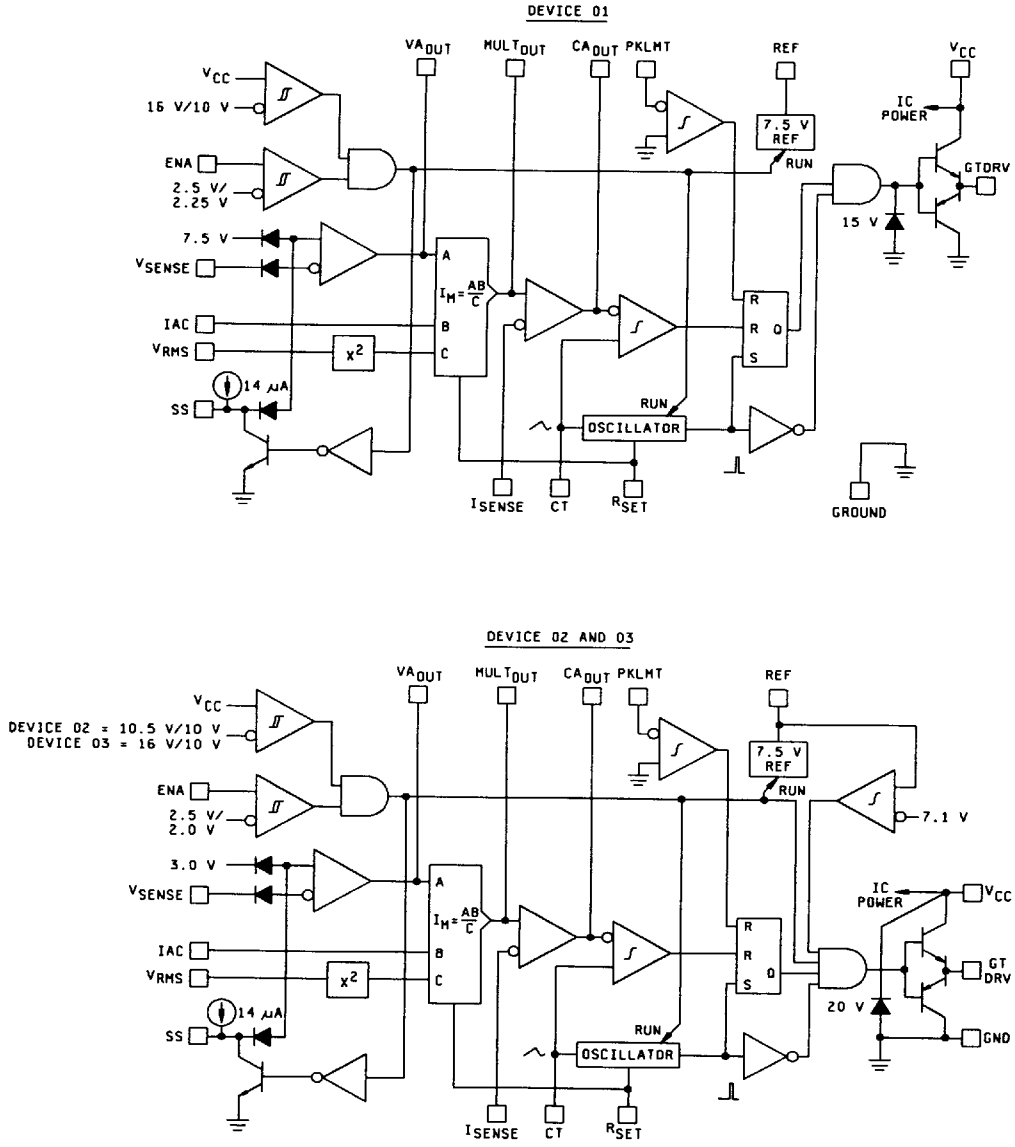


FIGURE 2. Block diagram.

TABLE II. Electrical test requirements.

Test requirements	Subgroups (in accordance with MIL-STD-883, TM 5005, table I)	Subgroups (in accordance with MIL-I-38535, table III)	
	Device class M	Device class Q	Device class V
Interim electrical parameters (see 4.2)	1	1	1
Final electrical parameters (see 4.2)	1/ 1, 2, 3, 4, 5, 6	1/ 1, 2, 3, 4, 5, 6	1/ 1, 2, 3, 4, 5, 6
Group A test requirements (see 4.4)	1, 2, 3, 4, 5, 6	1, 2, 3, 4, 5, 6	1, 2, 3, 4, 5, 6
Group C end-point electrical parameters (see 4.4)	1	1, 2, 3	1, 2, 3
Group D end-point electrical parameters (see 4.4)	1	1, 2, 3	1, 2, 3
Group E end-point electrical parameters (see 4.4)	---	---	---

1/ PDA applies to subgroup 1.

4.2.1 Additional criteria for device class M.

a. Burn-in test, method 1015 of MIL-STD-883.

(1) Test condition A, B, C, or D. The test circuit shall be maintained by the manufacturer under document revision level control and shall be made available to the preparing or acquiring activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1015.

(2) T_A = +125°C, minimum.

b. Interim and final electrical test parameters shall be as specified in table II herein.

4.2.2 Additional criteria for device classes Q and V.

a. The burn-in test duration, test condition and test temperature, or approved alternatives shall be as specified in the device manufacturer's QM plan in accordance with MIL-I-38535. The burn-in test circuit shall be maintained under document revision level control of the device manufacturer's Technology Review Board (TRB) in accordance with MIL-I-38535 and shall be made available to the acquiring or preparing activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1015.

b. Interim and final electrical test parameters shall be as specified in table II herein.

c. Additional screening for device class V beyond the requirements of device class Q shall be as specified in appendix B of MIL-I-38535.

4.3 Qualification inspection for device classes Q and V. Qualification inspection for device classes Q and V shall be in accordance with MIL-I-38535. Inspections to be performed shall be those specified in MIL-I-38535 and herein for groups A, B, C, D, and E inspections (see 4.4.1 through 4.4.4).

4.4 Conformance inspection. Quality conformance inspection for device class M shall be in accordance with MIL-STD-883 (see 3.1 herein) and as specified herein. Inspections to be performed for device class M shall be those specified in method 5005 of MIL-STD-883 and herein for groups A, B, C, D, and E inspections (see 4.4.1 through 4.4.4). Technology conformance inspection for classes Q and V shall be in accordance with MIL-I-38535 including groups A, B, C, D, and E inspections and as specified herein except where option 2 of MIL-I-38535 permits alternate in-line control testing.

4.4.1 Group A inspection.

a. Tests shall be as specified in table II herein.

b. Subgroups 7, 8, 9, 10, and 11 in table I, method 5005 of MIL-STD-883 shall be omitted.

4.4.2 Group C inspection. The group C inspection end-point electrical parameters shall be as specified in table II herein.

4.4.2.1 Additional criteria for device class M. Steady-state life test conditions, method 1005 of MIL-STD-883:

a. Test condition A, B, C, or D. The test circuit shall be maintained by the manufacturer under document revision level control and shall be made available to the preparing or acquiring activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1005.

b. T_A = +125°C, minimum.

c. Test duration: 1,000 hours, except as permitted by method 1005 of MIL-STD-883.

4.4.2.2 Additional criteria for device classes Q and V. The steady-state life test duration, test condition and test temperature, or approved alternatives shall be as specified in the device manufacturer's QM plan in accordance with MIL-I-38535. The test circuit shall be maintained under document revision level control by the device manufacturer's TRB, in accordance with MIL-I-38535, and shall be made available to the acquiring or preparing activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1005.

4.4.3 Group D inspection. The group D inspection end-point electrical parameters shall be as specified in table II herein.

4.4.4 Group E inspection. Group E inspection is required only for parts intended to be marked as radiation hardness assured (see 3.5 herein). RHA levels for device classes Q and V shall be M, D, L, R, F, G, and H and for device class M shall be M and D.

a. End-point electrical parameters shall be as specified in table II herein.

b. For device class M, the devices shall be subjected to radiation hardness assured tests as specified in MIL-I-38535, appendix A, for the RHA level being tested. For device classes Q and V, the devices or test vehicle shall be subjected to radiation hardness assured tests as specified in MIL-I-38535 for the RHA level being tested. All device classes must meet the postirradiation end-point electrical parameter limits as defined in table I at T_A = +25°C ±5°C, after exposure, to the subgroups specified in table II herein.

c. When specified in the purchase order or contract, a copy of the RHA delta limits shall be supplied.

5. PACKAGING

5.1 Packaging requirements. The requirements for packaging shall be in accordance with MIL-STD-883 (see 3.1 herein) for device class M and MIL-I-38535 for device classes Q and V.

6. NOTES

6.1 Intended use. Microcircuits conforming to this drawing are intended for use for Government microcircuit applications (original equipment), design applications, and logistics purposes.

6.1.1 Replaceability. Microcircuits covered by this drawing will replace the same generic device covered by a contractor-prepared specification or drawing.

6.1.2 Substitutability. Device class Q devices will replace device class M devices.

6.2 Configuration control of SMD's. All proposed changes to existing SMD's will be coordinated with the users of record for the individual documents. This coordination will be accomplished in accordance with MIL-STD-973 using DD Form 1692, Engineering Change Proposal.

6.3 Record of users. Military and industrial users shall inform Defense Electronics Supply Center when a system application requires configuration control and which SMD's are applicable to that system. DESC will maintain a record of users and this list will be used for coordination and distribution of changes to the drawings. Users of drawings covering microelectronic devices (FSC 5962) should contact DESC-EC, telephone (513) 296-6047.

6.4 Comments. Comments on this drawing should be directed to DESC-EC, Dayton, Ohio 45444-5270, or telephone (513) 296-5377.

6.5 Abbreviations, symbols, and definitions. The abbreviations, symbols, and definitions used herein are defined in MIL-I-38535 and MIL-STD-1331.

6.6 One part - one part number system. The one part - one part number system described below has been developed to allow for transitions between identical generic devices covered by the three major microcircuit requirements documents (MIL-H-38534, MIL-I-38535, and 1.2.1 of MIL-STD-883) without the necessity for the generation of unique PIN's. The three military requirements documents represent different class levels, and previously when a device manufacturer upgraded military product from one class level to another, the benefits of the upgraded product were unavailable to the Original Equipment Manufacturer (OEM), that was contractually locked into the original unique PIN. By establishing a one part number system covering all three documents, the OEM can acquire to the highest class level available for a given generic device to meet system needs without modifying the original contract parts selection criteria.

Military documentation format	Example PIN under new system	Manufacturing source listing	Document listing
New MIL-H-38534 Standard Microcircuit Drawings	5962-XXXXXZZ(H or K)YY	QML-38534	MIL-BUL-103
New MIL-I-38535 Standard Microcircuit Drawings	5962-XXXXXZZ(Q or V)YY	QML-38535	MIL-BUL-103
New 1.2.1 of MIL-STD-883 Standard Microcircuit Drawings	5962-XXXXXZZ(M)YY	MIL-BUL-103	MIL-BUL-103

6.7 Sources of supply.

6.7.1 Sources of supply for device classes Q and V. Sources of supply for device classes Q and V are listed in QML-38535. The vendors listed in QML-38535 have submitted a certificate of compliance (see 3.6 herein) to DESC-EC and have agreed to this drawing.

6.7.2 Approved sources of supply for device class M. Approved sources of supply for class M are listed in MIL-BUL-103. The vendors listed in MIL-BUL-103 have agreed to this drawing and a certificate of compliance (see 3.6 herein) has been submitted to and accepted by DESC-EC.